WNSC6D16650B



Silicon Carbide Diode Rev.01 - 25 January 2022

Product data sheet

1. General description

Silicon Carbide Schottky diode in a TO263 (D2PAK) plastic package, designed for high frequency switched-mode power supplies.



2. Features and benefits

- New 6th Generation Technology
- Low Forward Voltage Drop
- Low Reverse Leakage Current
- High Forward Surge Capability I_{FSM}
- Reduced losses in associated MOSFET
- Reduced EMI
- Reduced cooling requirements
- RoHS compliant

3. Applications

- Power factor correction
- Telecom / Server SMPS
- UPS
- PV inverter
- PC Silverbox
- LED / OLED TV
- Motor Drives

4. Quick reference data

Table 1. Q	uick reference data						
Symbol	Parameter	Conditions	Values			Unit	
Absolute	maximum rating						
V_{RRM}	repetitive peak reverse voltage			6	50		V
$I_{F(AV)}$	average forward current	δ = 0.5 ; square-wave pulse; T _{mb} ≤ 139 °C; Fig. 1; Fig. 2; Fig. 3		16		A	
Tj	junction temperature			175		°C	
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Static ch	aracteristics						
V _F	forward voltage	I _F = 16 A; T _j = 25 °C; <u>Fig. 5</u>		-	1.29	1.45	V
		I _F = 16 A; T _j = 150 °C; <u>Fig. 5</u>		-	1.45	1.65	V
Dynamic	characteristics						
Q _r	recovered charge	$I_F = 16 \text{ A}; \text{ d}I_F/\text{d}t = 500 \text{ A}/\mu\text{s}; \text{ V}_R = 400 \text{ V};$ $T_j = 25 \text{ °C}; \text{ Fig. 7}$		-	36	-	nC

5. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	n.c.	not connected	Free Fil	К-Ң-А
2	К	cathode [1]		001aaa020
3	А	anode		
mb	К	mounting base; connected to cathode	1 TO-263 (D2PAK)	

[1] It is not possible to connect to pin 2 of the TO263 package.

6. Ordering information

Table 3. Ordering information								
Type number	Package	Orderable part number	Packing	Small packing	Package	Package		
	name		method	quantity	version	issue date		
WNSC6D16650B	TO263	WNSC6D16650B6J	Reel	800	TO263N	26-Sep-2016		

7. Marking

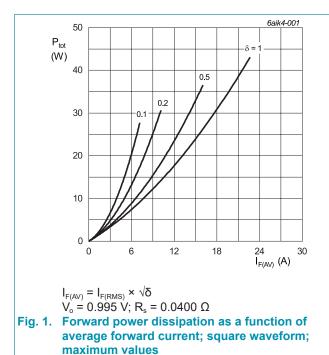
Table 4. Marking codes					
Type number	Marking codes				
WNSC6D16650B	WNSC6D 16650B				

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
V _{RRM}	repetitive peak reverse voltage		650	V
V_{RWM}	crest working reverse voltage		650	V
V _R	reverse voltage	DC	650	V
$I_{\rm F(AV)}$	average forward current	δ = 0.5; square-wave pulse; T _{mb} ≤ 139 °C; Fig. 1; Fig. 2; Fig. 3	16	A
I _{FRM}	repetitive peak forward current	δ = 0.5; t _p = 25 μs; T _{mb} ≤ 139 °C; square-wave pulse	32	A
I _{FSM}	non-repetitive peak	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse	110	А
	forward current	t_p = 10 µs; $T_{j(init)}$ = 25 °C; square-wave pulse	900	А
l ² t	I ² t for fusing	sine-wave pulse; $T_{j(init)}$ = 25 °C; t_p = 10 ms	61	A ² s
T _{stg}	storage temperature		-55 to 175	°C
T _j	junction temperature		175	°C



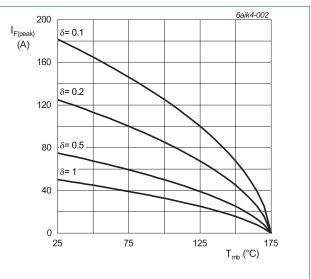
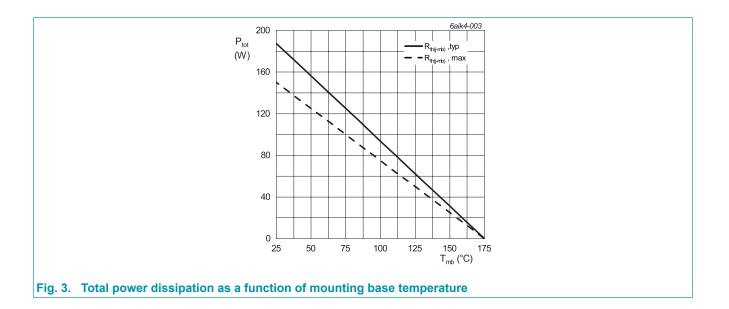


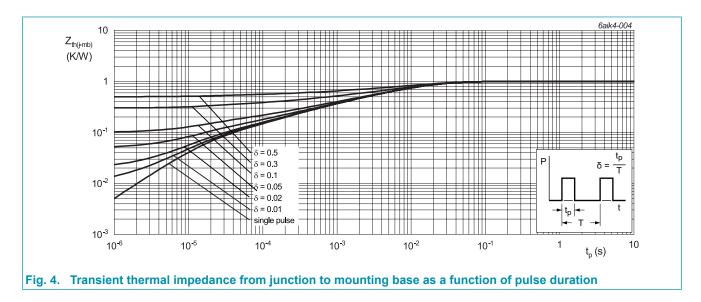
Fig. 2. Current derating as a function of mounting base temperature

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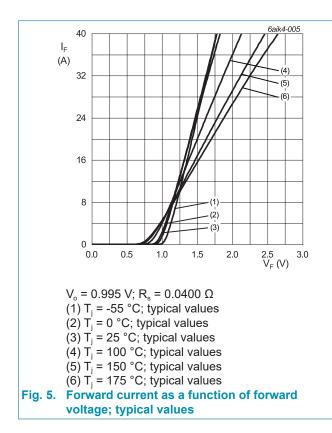
9. Thermal characteristics

Table 6. Th	ermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	<u>Fig. 4</u>	-	0.8	1	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient free air	in free air	-	50	-	K/W



10. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
$V_{\rm F}$	forward current	I _F = 16 A; T _j = 25 °C; <u>Fig. 5</u>	-	1.29	1.45	V
		I _F = 16 A; T _j = 150 °C; <u>Fig. 5</u>	-	1.45	1.65	V
		I _F = 16 A; T _j = 175 °C; <u>Fig. 5</u>	-	1.50	1.7	V
I _R	reverse current	V _R = 650 V; T _j = 25 °C; <u>Fig. 6</u>	-	1	80	μA
		V _R = 650 V; T _j = 175 °C; <u>Fig. 6</u>	-	25	320	μA
Dynamic	characteristics				_	
Q _r	recovered charge	$I_F = 16 \text{ A}; V_R = 400 \text{ V}; \text{ d}I_F/\text{d}t = 500 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; \text{ Fig. 7}$	-	36	-	nC
C _d	diode capacitance	f = 1 MHz; V _R = 1 V; T _j = 25 °C	-	780	-	pF
		f = 1 MHz; V _R = 300 V; T _j = 25 °C	-	86	-	pF
		f = 1 MHz; V _R = 600 V; T _j = 25 °C	-	79	-	pF
E _{as}	non-repetitive avalanche energy	I _R = 7 A; L = 5 mH; T _{j(init)} = 25 °C	120	-	-	mJ



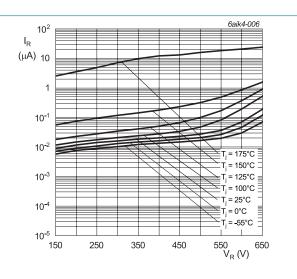
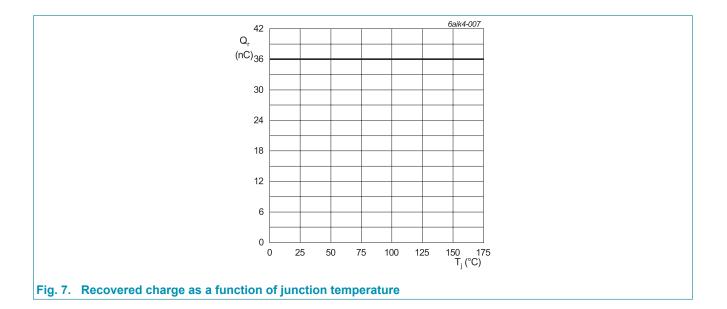


Fig. 6. Reverse leakage current as a function of reverse voltage; typical value

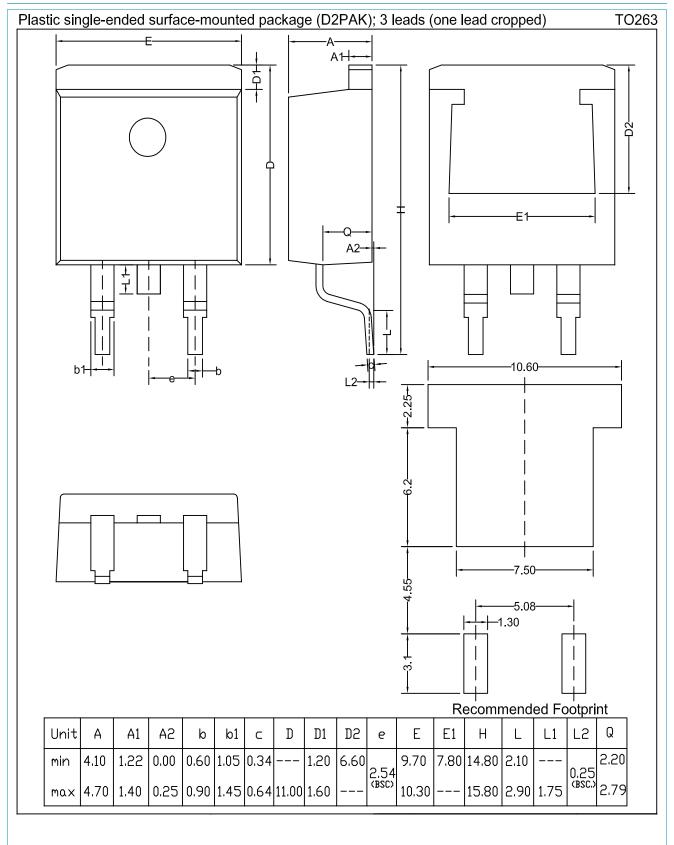
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11. Package outline



WNSC6D16650B Product data sheet All information provided in this document is subject to legal disclaimers. 25 January 2022

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12. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

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